# **General Purpose Transistor**

## **PNP Silicon**

#### **Features**

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CEO}$	-45	Vdc
Collector-Base Voltage	$V_{CBO}$	-60	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	Vdc
Collector Current – Continuous	Ic	-800	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

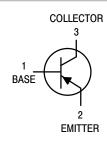
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 1) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

- 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina =  $0.4 \times 0.3 \times 0.024$  in 99.5% alumina.



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SOT-23 CASE 318 STYLE 6

#### **MARKING DIAGRAM**



DG = Specific Device Code

M = Date Code\*

= Pb-Free Package

(Note: Microdot may be in either location)
\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>		
BCW68GLT1G, NSVBCW68GLT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel		
BCW68GLT3G	SOT-23 (Pb-Free)	10000 / Tape & Reel		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

### **ELECTRICAL CHARACTERISTICS** ( $T_A = 25$ °C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•				
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = –10 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	-45	-	_	Vdc
Collector–Emitter Breakdown Voltage $(I_C = -10 \mu Adc, V_{EB} = 0)$	V <sub>(BR)CES</sub>	-60	-	-	Vdc
Emitter–Base Breakdown Voltage $(I_E = -10 \mu Adc, I_C = 0)$	V <sub>(BR)EBO</sub>	-5.0	_	_	Vdc
Collector Cutoff Current $(V_{CE}=-45 \text{ Vdc}, I_E=0)$ $(V_{CE}=-45 \text{ Vdc}, I_B=0, T_A=150^{\circ}\text{C})$	ICES	_ _	_ _	-20 -10	nAdc μAdc
Emitter Cutoff Current (V <sub>EB</sub> = -4.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	_	_	-20	nAdc
ON CHARACTERISTICS					
DC Current Gain $ \begin{aligned} &(I_C = -10 \text{ mAdc, } V_{CE} = -1.0 \text{ Vdc)} \\ &(I_C = -100 \text{ mAdc, } V_{CE} = -1.0 \text{ Vdc)} \\ &(I_C = -300 \text{ mAdc, } V_{CE} = -1.0 \text{ Vdc)} \end{aligned} $	h <sub>FE</sub>	120 160 60	- - -	400 _ _	1
Collector–Emitter Saturation Voltage (I <sub>C</sub> = -500 mAdc, I <sub>B</sub> = -50 mAdc)	V <sub>CE(sat)</sub>	-	_	-0.7	Vdc
Base–Emitter Saturation Voltage (I <sub>C</sub> = –500 mAdc, I <sub>B</sub> = –50 mAdc)	V <sub>BE(sat)</sub>	-	_	-2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS		•			-
Current–Gain – Bandwidth Product $(I_C = -20 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}, f = 100 \text{ MHz})$	f <sub>T</sub>	100	_	_	MHz
Output Capacitance $(V_{CB}=-10 \text{ Vdc}, I_E=0, f=1.0 \text{ MHz})$	C <sub>obo</sub>	-	_	18	pF
Input Capacitance ( $V_{EB}$ = -0.5 Vdc, $I_C$ = 0, f = 1.0 MHz)	C <sub>ibo</sub>	-	_	105	pF
Noise Figure (I <sub>C</sub> = $-0.2$ mAdc, V <sub>CE</sub> = $-5.0$ Vdc, R <sub>S</sub> = $1.0$ k $\Omega$ , f = $1.0$ kHz, BW = $200$ Hz)	N <sub>F</sub>	-	_	10	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### TYPICAL CHARACTERISTICS

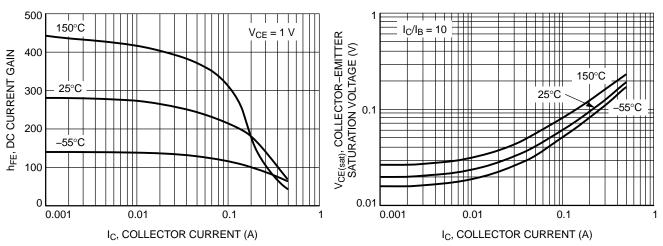


Figure 1. DC Current Gain vs. Collector Current

Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

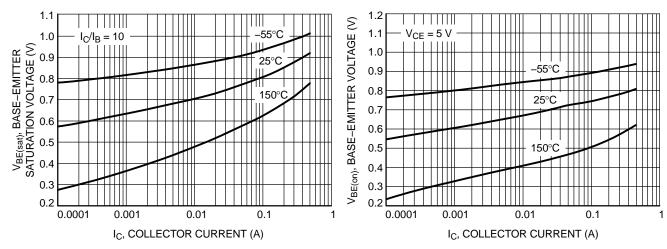


Figure 3. Base Emitter Saturation Voltage vs.
Collector Current

Figure 4. Base Emitter Voltage vs. Collector
Current

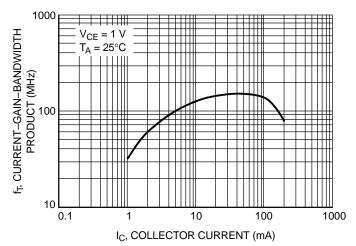


Figure 5. Current Gain Bandwidth Product vs. Collector Current

#### TYPICAL CHARACTERISTICS

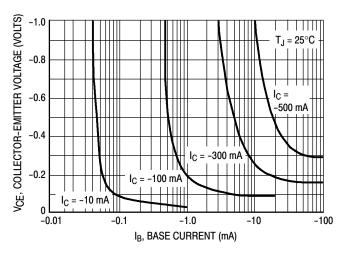


Figure 6. Saturation Region

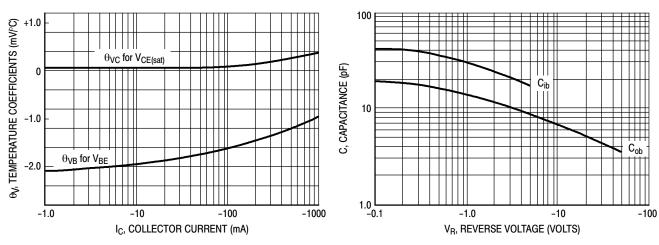
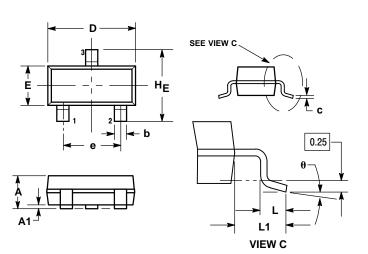


Figure 7. Temperature Coefficients

Figure 8. Capacitances

#### PACKAGE DIMENSIONS

#### SOT-23 (TO-236) CASE 318-08 **ISSUE AP**



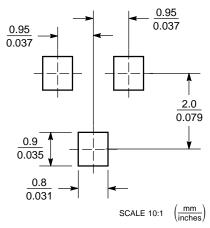
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 198.
  CONTROLLING DIMENSION: INCH.
  MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH
  THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM
  THICKNESS OF BASE MATERIAL.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
  DISTRIBUTION OF ANTE PURPOR
- PROTRUSIONS, OR GATE BURRS

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.89	1.00	1.11	0.035	0.040	0.044	
A1	0.01	0.06	0.10	0.001	0.002	0.004	
b	0.37	0.44	0.50	0.015	0.018	0.020	
С	0.09	0.13	0.18	0.003	0.005	0.007	
D	2.80	2.90	3.04	0.110	0.114	0.120	
E	1.20	1.30	1.40	0.047	0.051	0.055	
е	1.78	1.90	2.04	0.070	0.075	0.081	
L	0.10	0.20	0.30	0.004	0.008	0.012	
L1	0.35	0.54	0.69	0.014	0.021	0.029	
HE	2.10	2.40	2.64	0.083	0.094	0.104	
Δ	00		100	00		100	

STYLE 6: PIN 1.

- BASE
- 2. EMITTER
- COLLECTOR

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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